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電源管理



顯示驅動



二三極管



LDO穩壓器



觸摸芯片



MOS管



運算放大器



存儲芯片



MCU



串口通信

RS1M

產品規格說明書

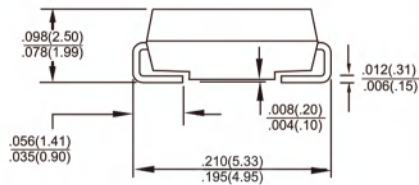
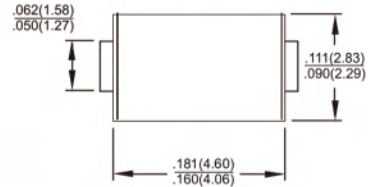


Features

- ✧ UL Recognized File # E-326243
- ✧ For surface mounted application
- ✧ Glass passivated junction chip
- ✧ Built-in strain relief, ideal for automated placement
- ✧ Plastic material used carries Underwriters Laboratory Classification 94V-0
- ✧ Fast switching for high efficiency
- ✧ High temperature soldering: 260°C/ 10 seconds at terminals
- ✧ Green compound with suffix "G" on packing code & prefix "G" on datecode.

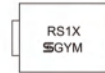
Mechanical Data

- ✧ Cases: Molded plastic
- ✧ Terminals: Pure tin plated, Lead free.
- ✧ Polarity: Indicated by cathode band
- ✧ Packing: 12mm tape per EIA STD RS-481
- ✧ Weight: 0.064 grams



Dimensions in inches and (millimeters)

Marking Diagram



RS1X = Specific Device Code
G = Green Compound
Y = Year
M = Work Month

Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	RS 1A	RS 1B	RS 1D	RS 1G	RS 1J	RS 1K	RS 1M	Units
Maximum Recurrent Peak Reverse Voltage	VRRM	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	VRMS	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	VDC	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current See Fig. 1 @T _L =90 °C	IF(AV)	1.0							A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	IFSM	30							A
Maximum Instantaneous Forward Voltage @ 1.0A	VF	1.3							V
Maximum DC Reverse Current at @ T _A =25 °C Rated DC Blocking Voltage (Note 1) @ T _A =125 °C	IR	5 50							uA uA
Maximum Reverse Recovery Time (Note 4)	Trr	150				250	500		nS
Typical Junction Capacitance (Note 2)	Cj	10							pF
Typical Thermal Resistance (Note 3)	R θJA R θJL	105 32							°C /W
Operating Temperature Range	TJ	-55 to +150							°C
Storage Temperature Range	TSTG	-55 to +150							°C

Notes: 1. Pulse Test with PW=300 usec, 1% Duty Cycle

2. Measured at 1 MHz and Applied VR=4.0 Volts

3. Mounted on P.C.B. with 0.2"x0.2" (5.0 x 5.0 mm) Copper Pad Areas.

4. Reverse Recovery Test Conditions: I_F=0.5A, I_R=1.0A, I_{RR}=0.25A

Version: D10

RATINGS AND CHARACTERISTIC CURVES (RS1A THRU RS1M)

FIG.1- MAXIMUM FORWARD CURRENT DERATING CURVE

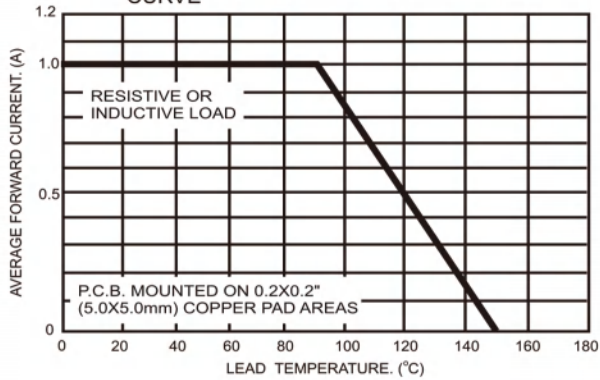


FIG.2- TYPICAL REVERSE CHARACTERISTICS

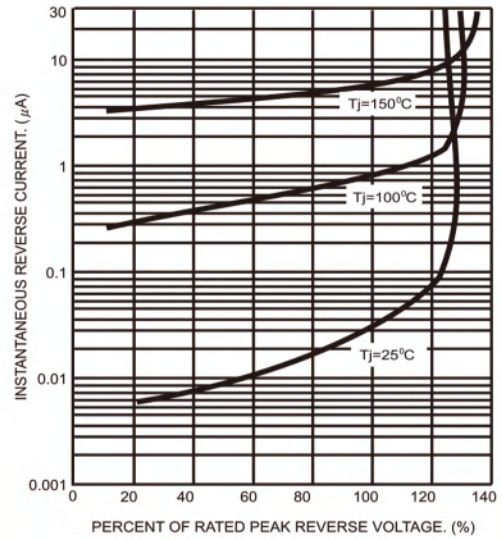


FIG.3- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

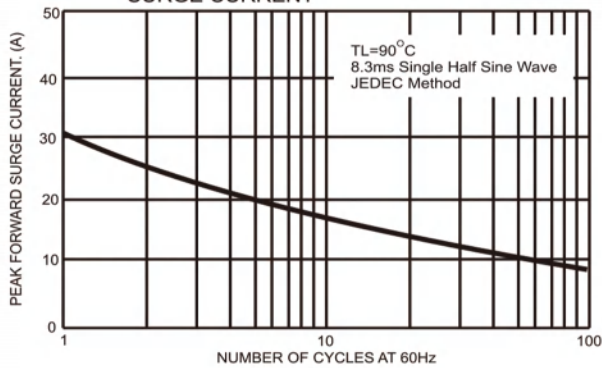


FIG.5- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS PER LEG

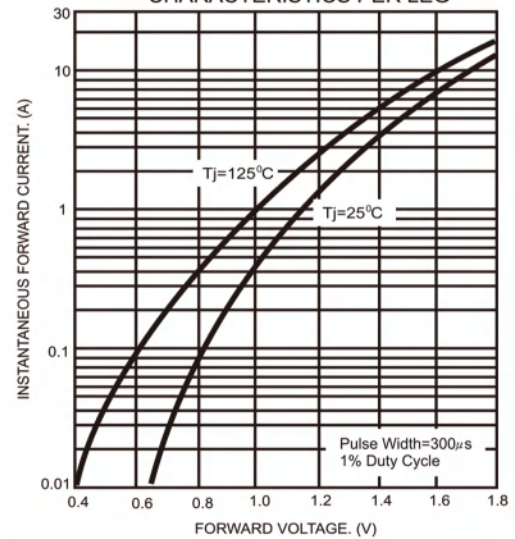


FIG.4- TYPICAL JUNCTION CAPACITANCE

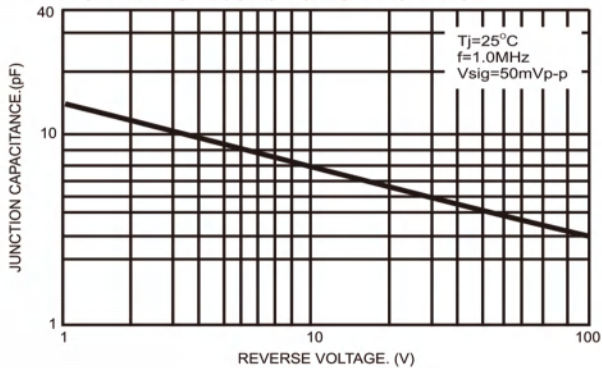
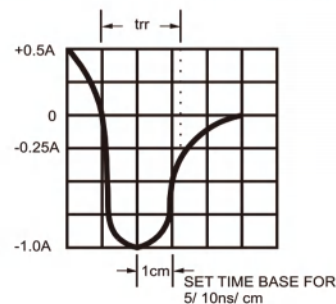
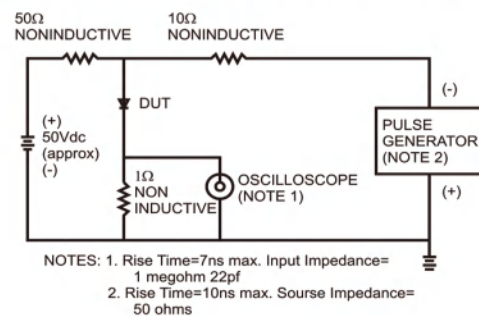


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM



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